

# N-channel TrenchMOS logic level FET Rev. 02 — 9 February 2011

Product data sheet

#### 1. **Product profile**

### 1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

### 1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

### 1.3 Applications

- 12 V, 24 V and 42 V loads
- Automotive systems

- General purpose power switching
- Motors, lamps and solenoids

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	100	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	-	46	Α
P <sub>tot</sub>	total power dissipation	$T_{mb} = 25  ^{\circ}\text{C}$ ; see Figure 2	-	-	157	W
Static chara	acteristics					
R <sub>DSon</sub> drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}$	-	22	27	mΩ	
	resistance	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 6}}{\text{Figure 7}};$	-	24	29	mΩ



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 46 \text{ A; } V_{sup} \leq 100 \text{ V;} \\ R_{GS} &= 50 \text{ \Omega; } V_{GS} = 5 \text{ V;} \\ T_{j(init)} &= 25 \text{ °C; } unclamped \end{split}$	-	-	152	mJ
Dynamic characteristics						
$Q_{GD}$	gate-drain charge	$V_{GS} = 5 \text{ V; } I_D = 25 \text{ A;}$ $V_{DS} = 80 \text{ V; } T_j = 25 \text{ °C;}$ see Figure 8	-	13	-	nC

# 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain[1]	mb	B
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

<sup>[1]</sup> It is not possible to make a connection to pin 2.

# 3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK9629-100B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	100	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$	-	100	V
$V_{GS}$	gate-source voltage		-15	15	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 5 V; see <u>Figure 1</u> ; see <u>Figure 3</u>	-	46	Α
		$T_{mb}$ = 100 °C; $V_{GS}$ = 5 V; see <u>Figure 1</u>	-	32	А
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; see Figure 3	-	186	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	157	W
T <sub>stg</sub>	storage temperature		-55	175	°C
T <sub>j</sub>	junction temperature		-55	175	°C
Source-drain	diode				
Is	source current	T <sub>mb</sub> = 25 °C	-	46	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	186	Α
Avalanche ru	iggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 46 A; $V_{sup} \le 100$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 5 V; $T_{j(init)}$ = 25 °C; unclamped	-	152	mJ

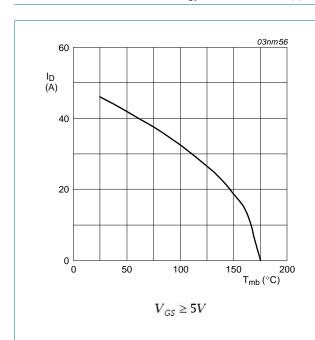


Fig 1. Normalized continuous drain current as a function of mounting base temperature

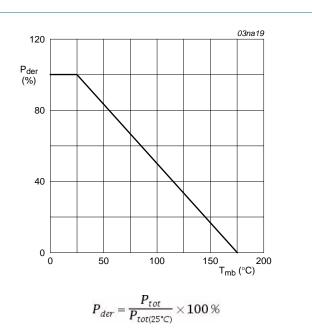
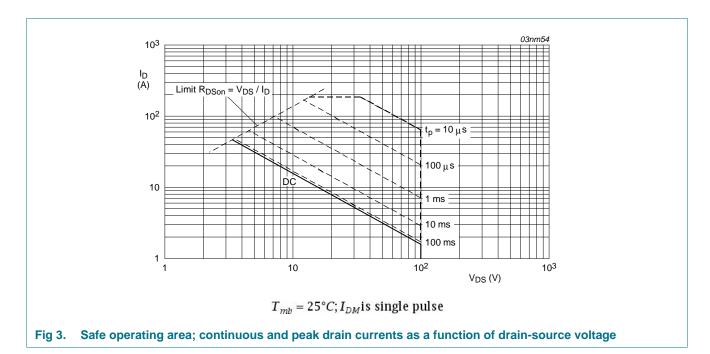


Fig 2. Normalized total power dissipation as a function of mounting base temperature



### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.95	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board	-	50	-	K/W

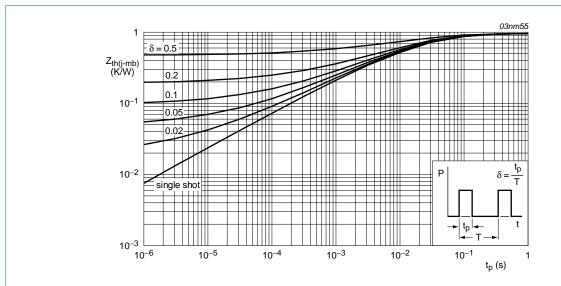


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

### 6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	89	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 25 \text{ °C}$ ; see Figure 5	1.1	1.5	2	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$ ; $T_j = -55$ °C; see <u>Figure 5</u>	-	-	2.3	V
		$I_D = 1 \text{ mA}$ ; $V_{DS} = V_{GS}$ ; $T_j = 175 \text{ °C}$ ; see Figure 5	0.5	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 15 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{GS} = -15 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	-	-	32	mΩ
	resistance	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 175 °C;$ see <u>Figure 6</u> ; see <u>Figure 7</u>	-	-	75	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C}$	-	22	27	mΩ
		$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 6</u> ; see <u>Figure 7</u>	-	24	29	mΩ
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 5 \text{ V};$	-	33	-	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C; see <u>Figure 8</u>	-	7	-	nC
$Q_{GD}$	gate-drain charge		-	13	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	3270	4360	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 9</u>	-	236	283	pF
$C_{rss}$	reverse transfer capacitance		-	103	141	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 5 \text{ V};$	-	30	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \Omega$ ; $T_j = 25 °C$	-	86	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	96	-	ns
t <sub>f</sub>	fall time		-	46	-	ns
L <sub>D</sub>	internal drain inductance	from upper edge of drain mounting base to centre of die; $T_j = 25$ °C	-	2.5	-	nΗ
		from drain lead 6 mm from package to centre of die; $T_j = 25$ °C	-	4.5	-	nΗ
L <sub>S</sub>	internal source inductance	from source lead to source bond pad; $T_j = 25  ^{\circ}\text{C}$	-	7.5	-	nΗ

Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drai	n diode					
V <sub>SD</sub>	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 10</u>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	114	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$	-	196	-	nC

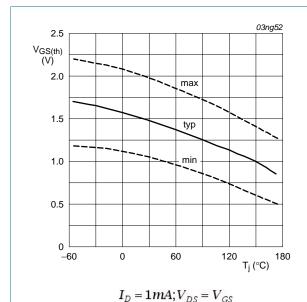
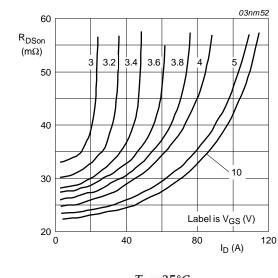


Fig 5. Gate-source threshold voltage as a function of junction temperature



 $T_j = 25^{\circ}C$ 

Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

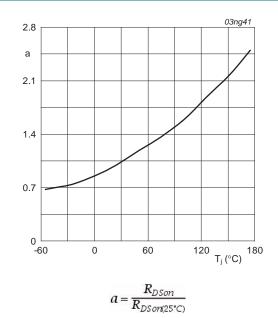
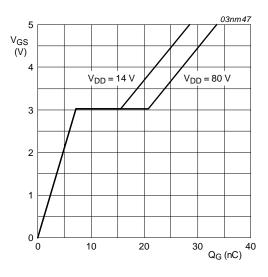


Fig 7. Normalized drain-source on-state resistance factor as a function of junction temperature



 $T_j = 25^{\circ}C; I_D = 25A$ 

Fig 8. Gate-source threshold voltage as a function of junction temperature

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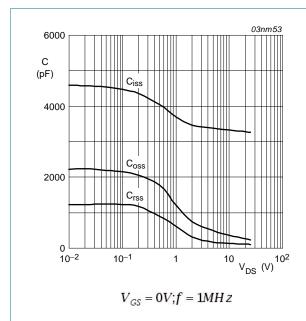


Fig 9. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

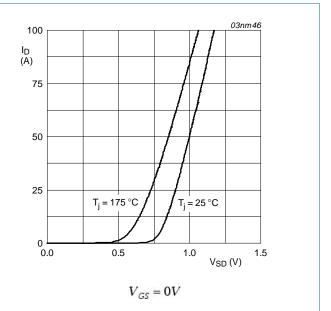


Fig 10. Source current as a function of source-drain voltage; typical values

### 7. Package outline

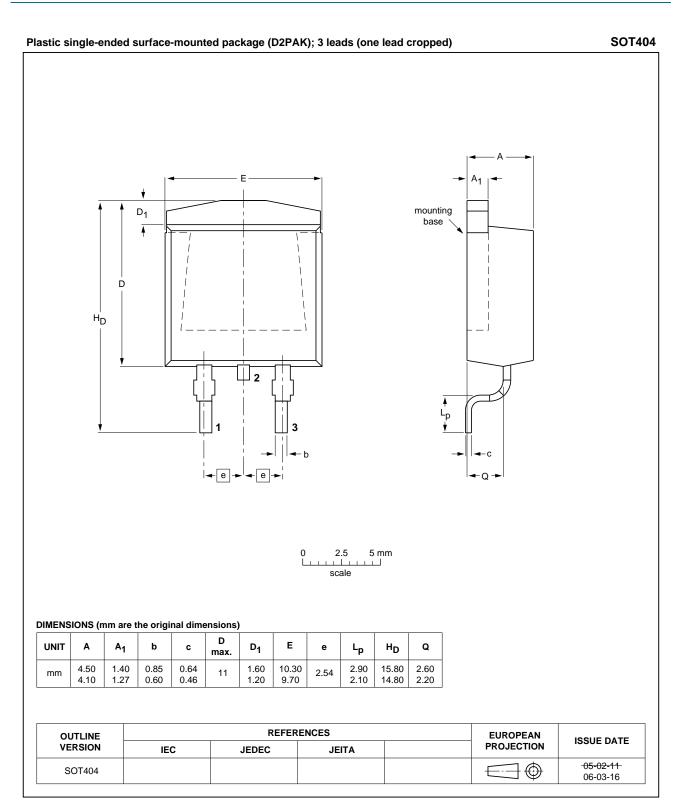


Fig 11. Package outline SOT404 (D2PAK)

# 8. Revision history

### Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK9629-100B v.2	20110209	Product data sheet	-	BUK95_9629_100B v.1
Modifications:	<ul> <li>The format of this data sheet has been redesigned to comply with the new identity g of NXP Semiconductors.</li> </ul>			the new identity guidelines
	<ul> <li>Legal texts have</li> </ul>	been adapted to the new	company name where	e appropriate.
	<ul> <li>Type number BL</li> </ul>	IK9629-100B separated f	rom data sheet BUK95	_9629_100B v.1.
BUK95_9629_100B v.1 (9397 750 11249)	20030418	Product data	-	-

### 9. Legal information

#### 9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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